

## ABSTRACT OF THE DISCLOSURE

In a solid-state image-sensing device, after completion of image sensing by individual pixels, in each pixel, a signal  $\phi_{VRB}$  fed to a capacitor C1 connected to the gate of a first MOS transistor T1 is turned to a high level to make it easy for a negative electric charge to flow into the MOS transistor T1. This permits quick recombination of the positive electric charges accumulated at the drain and gate of the MOS transistor T1, at the gate of a MOS transistor T2, at the anode of a photodiode, and in a capacitor C2, and thereby makes quick resetting possible.